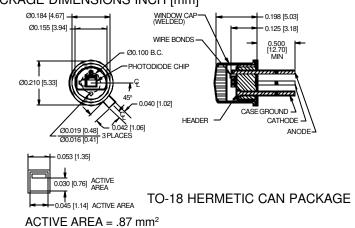
PHOTONIC DETECTORS INC PACKAGE DIMENSIONS INCH [mm]



Silicon Photodiode, Blue Enhanced Photovoltaic Isolated Type PDB-V102-I



FEATURES

- Low noise
- Blue enhanced
- · High shunt resistance
- High response

DESCRIPTION

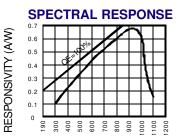
The PDB-V102-I is a silicon, PIN planar diffused, blue enhanced photodiode. Ideal for low noise photovoltaic applications. Packaged in a hermetic TO-18 metal can with a flat window and isolated ground lead.

APPLICATIONS

- Instrumentation
- · Character recognition
- Laser detection
- Industrial controls

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

				-
SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{BR}	Reverse Voltage		75	V
T _{stg}	Storage Temperature	-55	+150	°C
Τ _ο	Operating Temperature Range	-40	+125	°C
T _s	Soldering Temperature*		+240	°C
Ι	Light Current		0.5	mA



WAVELENGTH (nm)

*1/16 inch from case for 3 secs max

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{sc}	Short Circuit Current	H = 100 fc, 2850 K	7	8		mA
I _D	Dark Current	$H = 0, V_{_{\rm R}} = 10 \text{ V}$		40	125	pА
R _{sh}	Shunt Resistance	$H = 0, V_{_{R}} = 10 \text{ mV}$	2	10		GΩ
TC $R_{_{SH}}$	RSH Temp. Coefficient	$H = 0, V_{_{R}} = 10 \text{ mV}$		-8		% / °C
C	Junction Capacitance	$H = 0, V_{R} = 0 V^{**}$		250		pF
λrange	Spectral Application Range	Spot Scan	350		1100	nm
λρ	Spectral Response - Peak	Spot Scan		950		nm
V _{BR}	Breakdown Voltage	I = 10 m A	30	50		V
N EP	Noise Equivalent Power	V _R = 10 mV @ Peak		3x10 ⁻¹⁵		W/ V Hz
tr	Response Time	$RL = 1 K\Omega V_{R} = 0 V$		400		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. **f = 1 MHz